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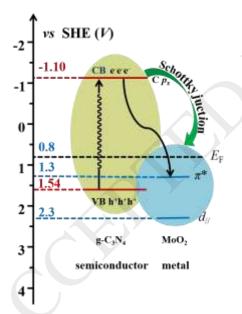
oxidative desulfurization

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Graphical abstract



The electronic structure of MoO₂/g-C₃N₄ metal-semiconductor heterojunction.

Highlights

• MoO₂/g-C₃N₄ composites have been successfully synthesized by a facile calcination method.

• Electron transfer from $g-C_3N_4$ to MoO_2 occurs for $MoO_2/g-C_3N_4$ heterojunction composites.

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